2SD1752, 2SD1752A

Silicon NPN epitaxial planar type

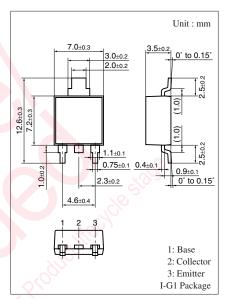
For power amplification and low-voltage switching Complementary to 2SB1148 and 2SB1148A

■ Features

- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- High-speed switching
- Satisfactory liniarity of forward current transfer ratio h_{FE}
- Large collector current I_C
- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment

■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SD1752	V_{CBO}	40	V
(Emitter open)	2SD1752A		50	
Collector-emitter voltage	2SD1752	V _{CEO}	20	V
(Base open)	2SD1752A		40	
Emitter-base voltage (Coll	V _{EBO}	5	V	
Collector current	I_{C}	10	A	
Peak collector current	I_{CP}	20	A	
Collector power dissipation	P _C	15	W	
	$T_a = 25^{\circ}C$		1.3	4011
Junction temperature	T_{j}	150	o °C	
Storage temperature	T_{stg}	-55 to +150	°C	



Note) Self-supported type package is also prepared.

■ Electrical Characteristics T_C = 25°C ± 3°C

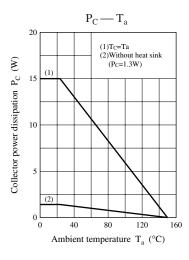
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SD1752	V _{CEO}	$I_C = 10 \text{ mA}, I_B = 0$	20	0		V
(Base open)	2SD1752A	9.		40			
Collector-base cutoff	2SD1752	I_{CBO}	$V_{CB} = 40 \text{ V}, I_{E} = 0$			50	μΑ
current (Emitter open)	2SD1752A		$V_{CB} = 50 \text{ V}, I_{E} = 0$			50	
Emitter-base cutoff current (Col	lector open)	I_{EBO}	$V_{EB} = 5 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer rat	io	h _{FE1}	$V_{CE} = 2 \text{ V}, I_{C} = 0.1 \text{ A}$	45			_
		h _{FE2} *	$V_{CE} = 2 \text{ V}, I_{C} = 3 \text{ A}$	90		260	
Collector-emitter saturation	voltage	V _{CE(sat)}	$I_C = 10 \text{ A}, I_B = 0.33 \text{ A}$			0.6	V
Base-emitter saturation volt	age	V _{BE(sat)}	$I_C = 10 \text{ A}, I_B = 0.33 \text{ A}$			1.5	V
Forward current transfer rat	io	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 10 \text{ MHz}$		120		MHz
Collector output capacitance		C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		200		pF
(Common base, input open	circuited)						
Turn-on time		t _{on}	$I_C = 3 \text{ A}, I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		0.3		μs
Storage time		t _{stg}	$V_{CC} = 20 \text{ V}$		0.4		μs
Fall time		t _f			0.1		μs

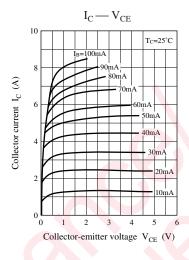
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

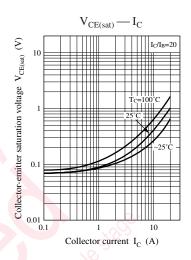
2. *: Rank classification

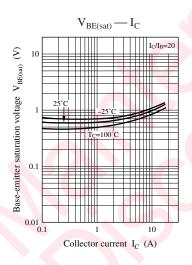
Rank	Q	Р		
h _{FE2}	90 to 180	130 to 260		

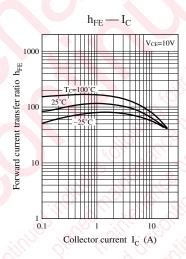
Panasonic

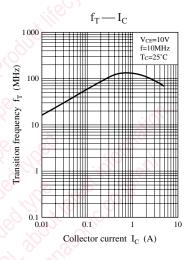


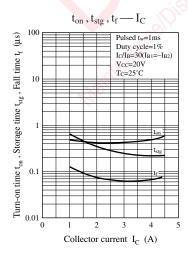


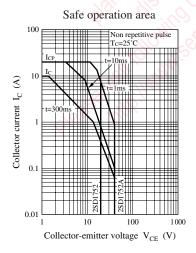




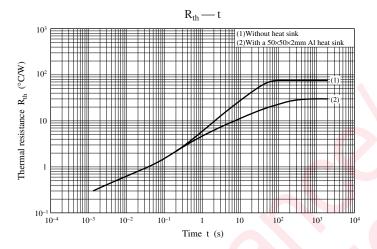








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